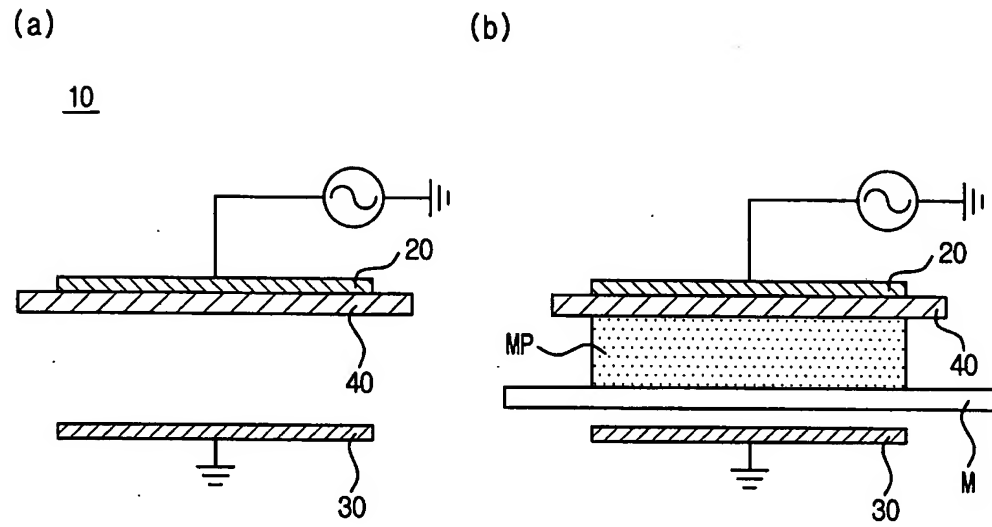


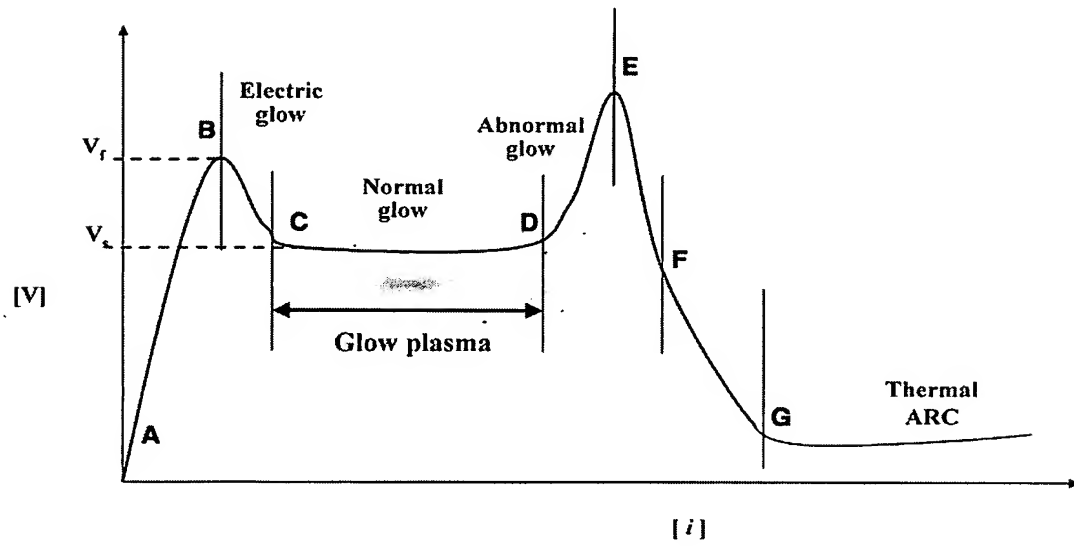
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**FIG. 1**



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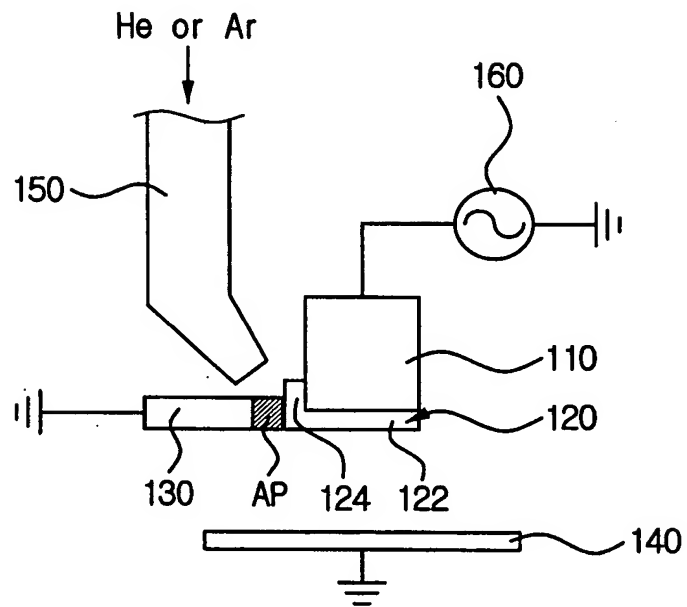
**FIG. 2**



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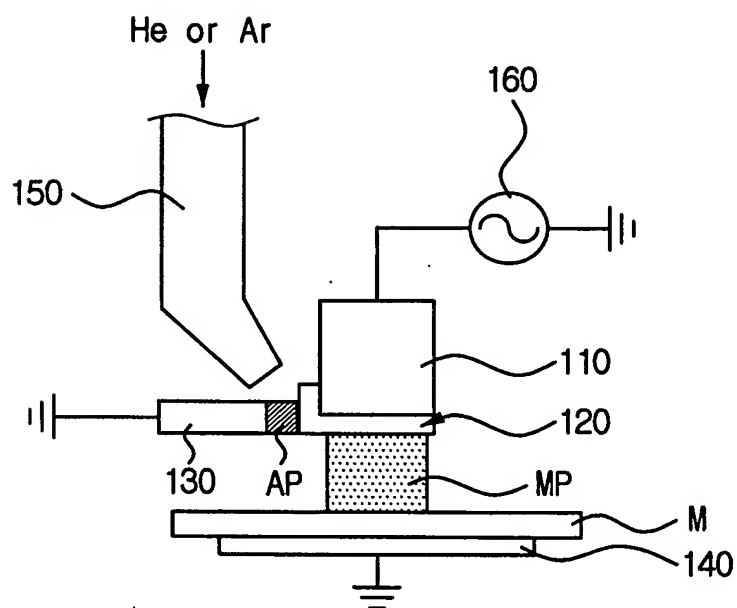
**FIG. 3**

100



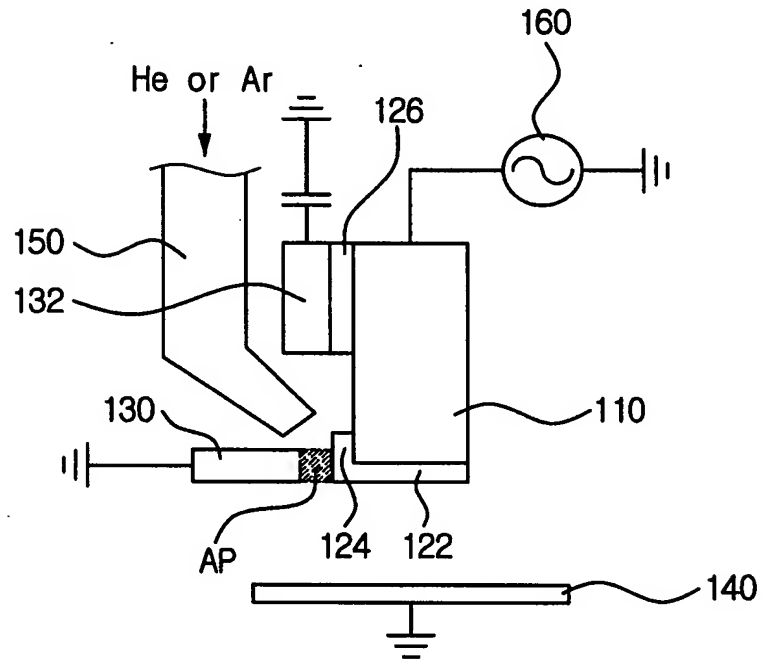
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**FIG. 4**



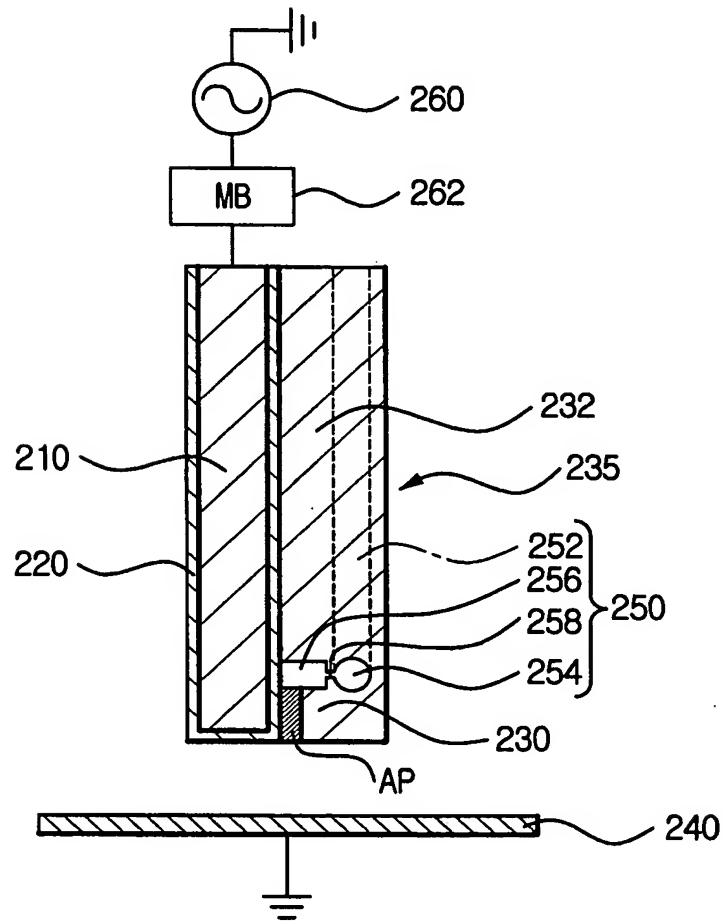
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**FIG. 5**



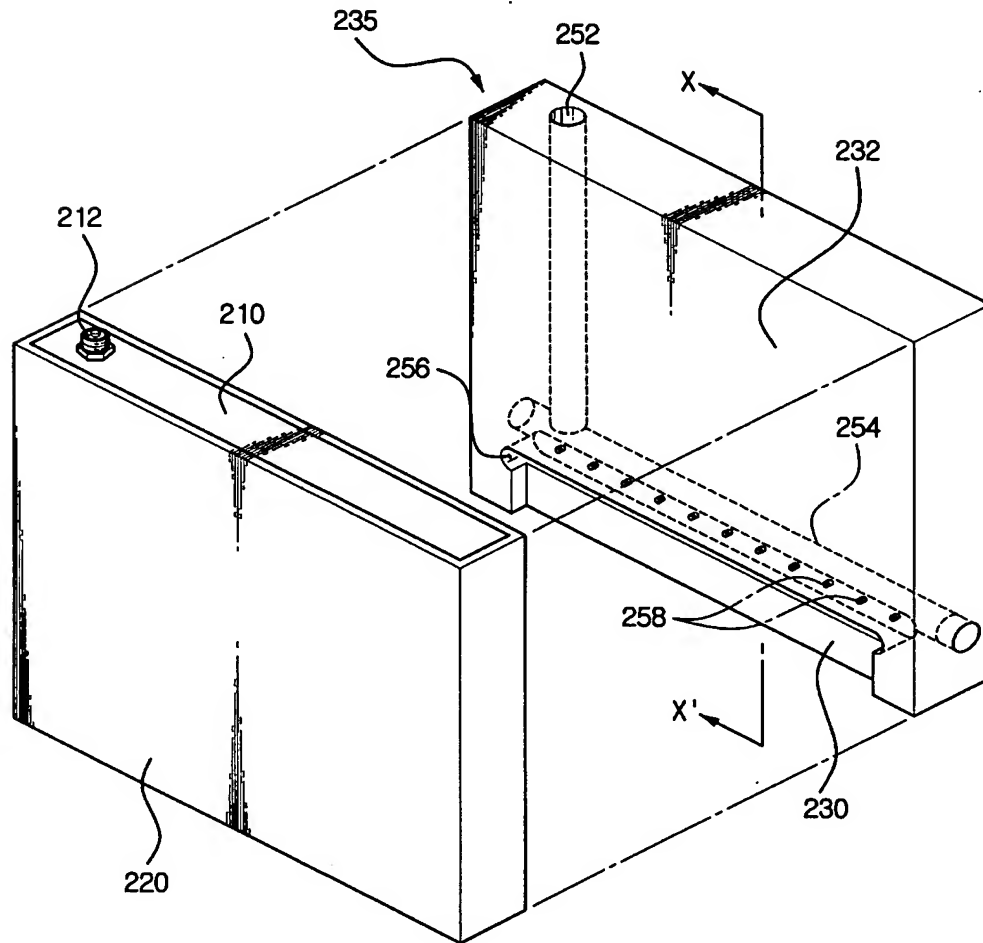
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**FIG. 6**



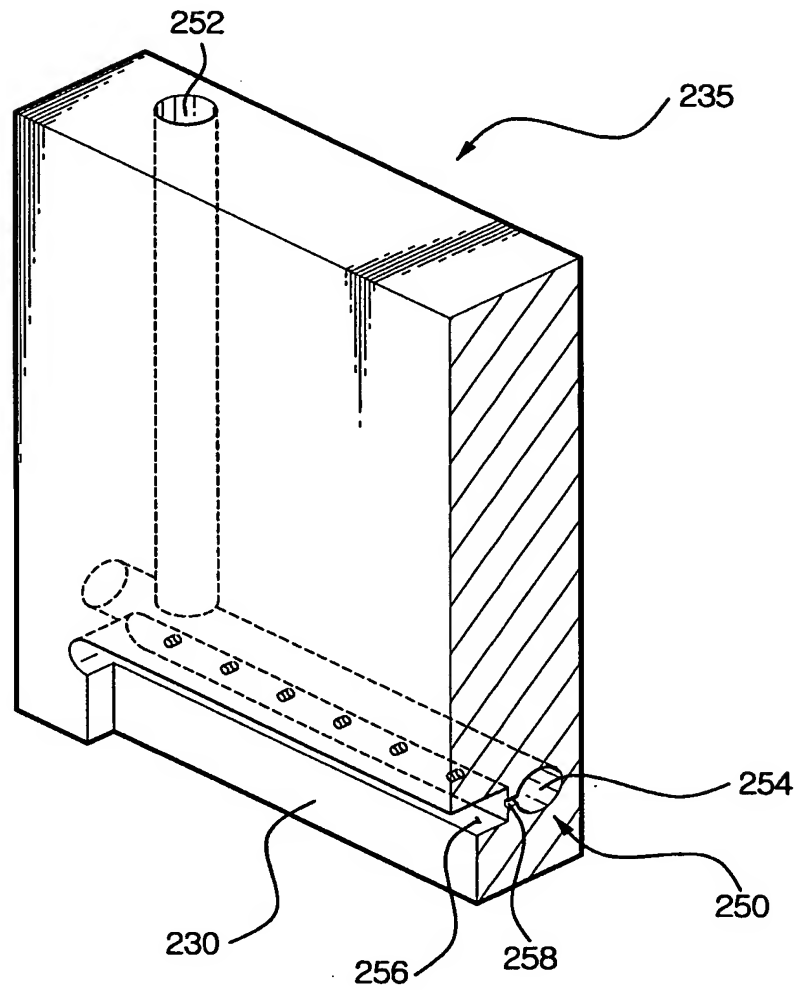
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**FIG. 7**



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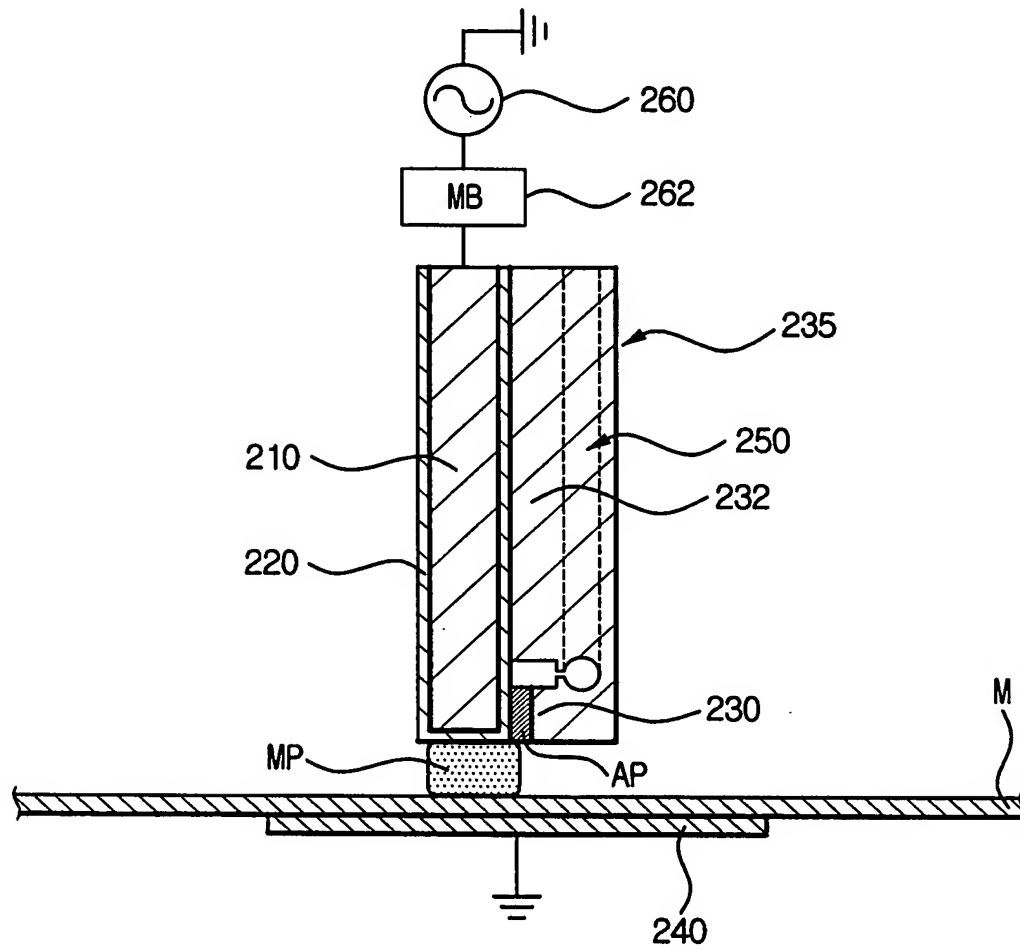
**FIG. 8**





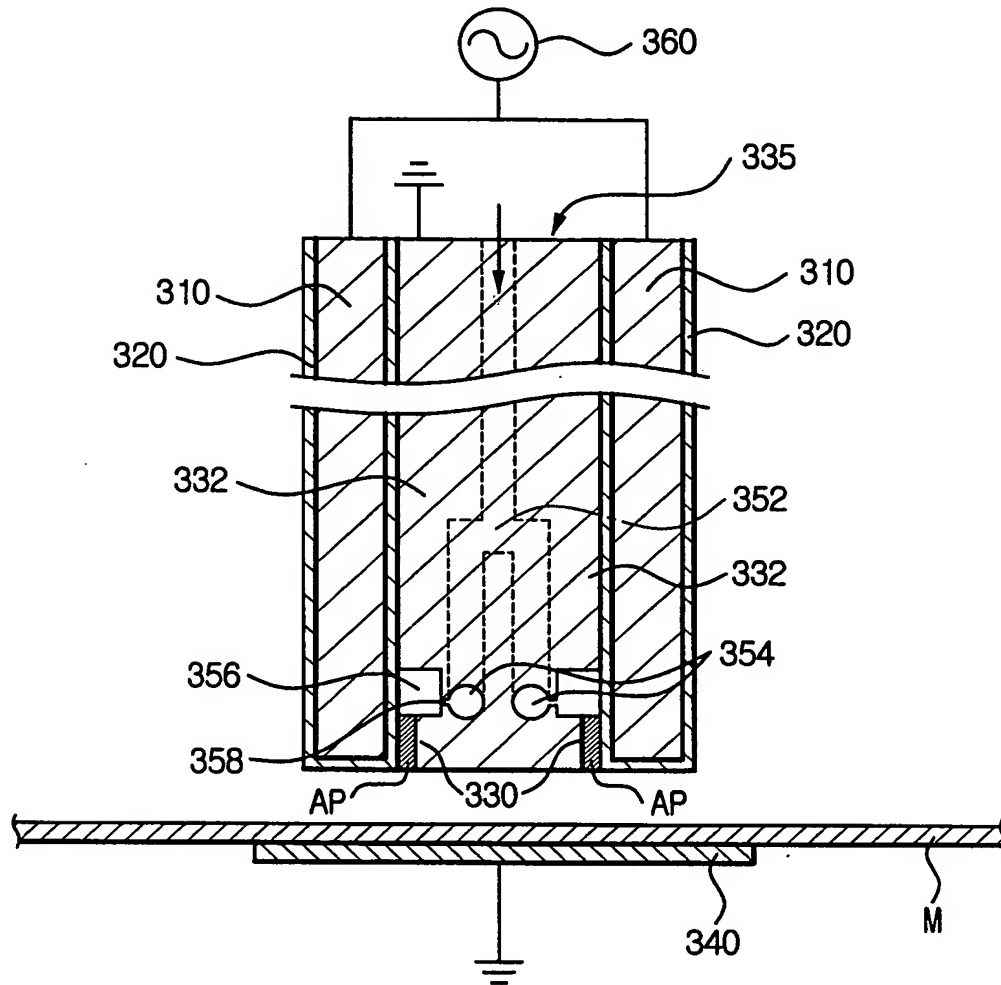
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FIG. 9



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**FIG. 10**

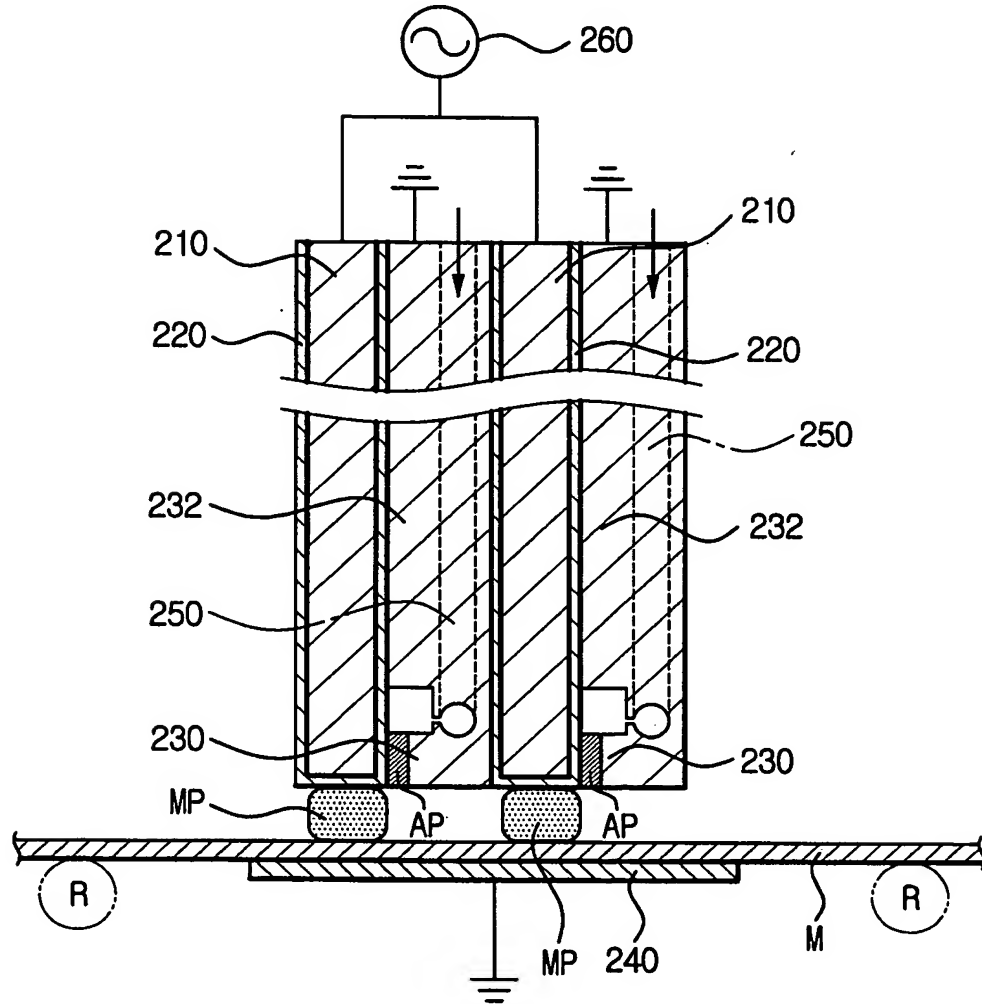




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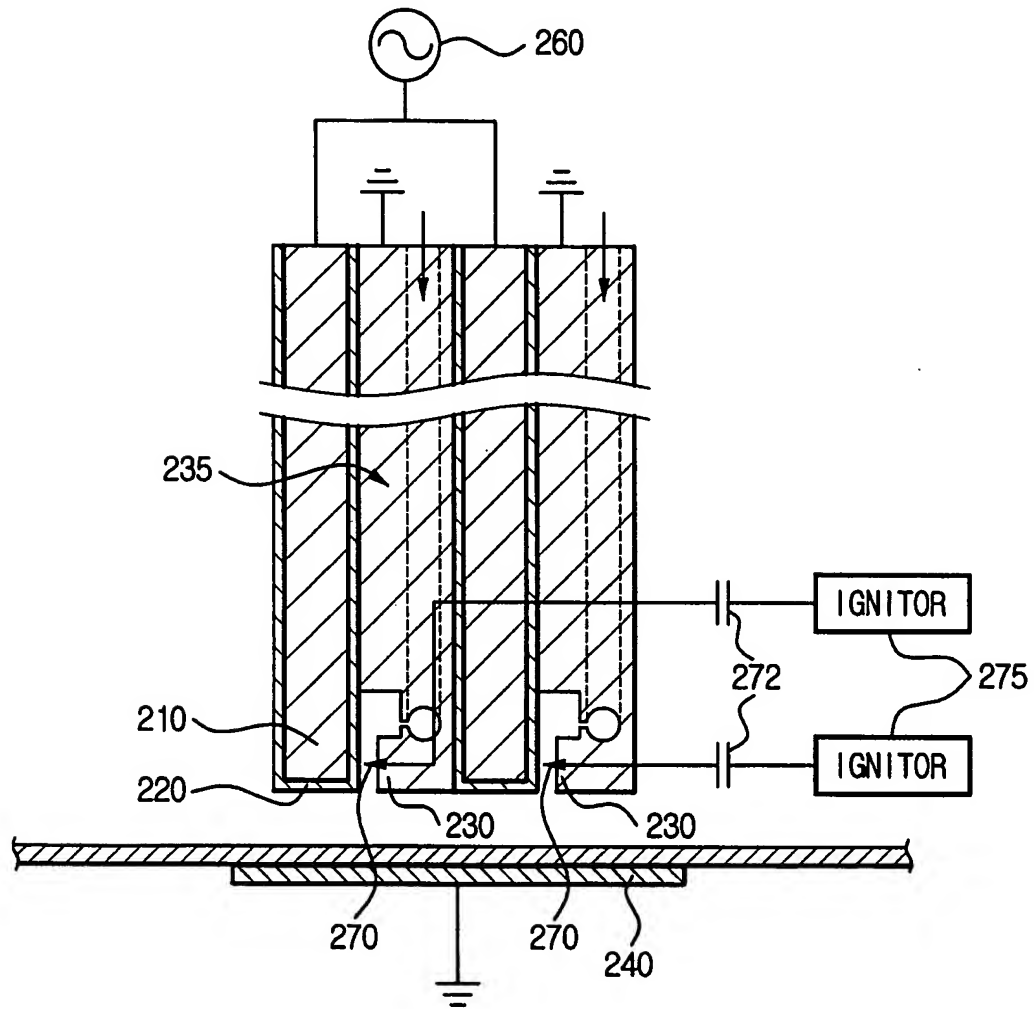
FIG. 12

201



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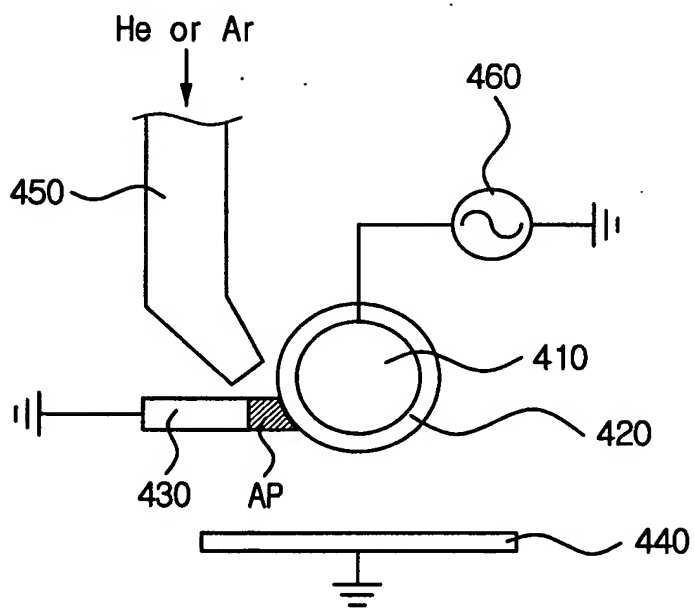
FIG. 13



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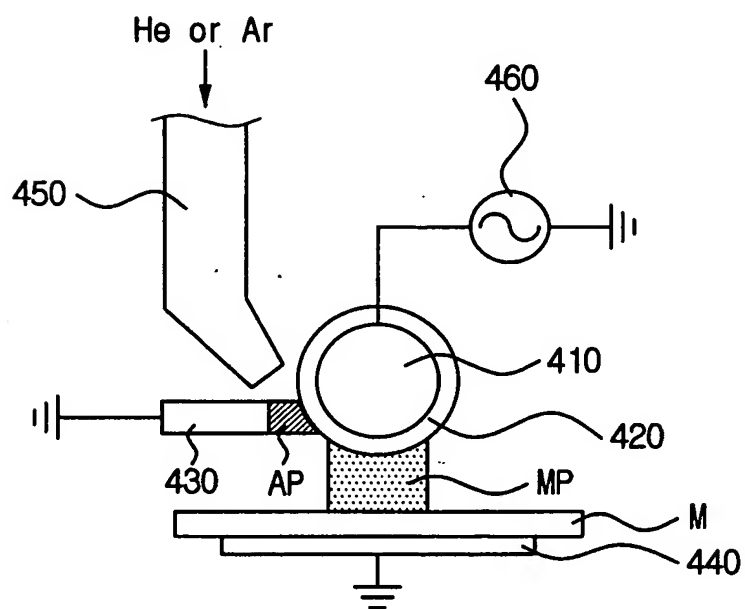
**FIG. 14**

400



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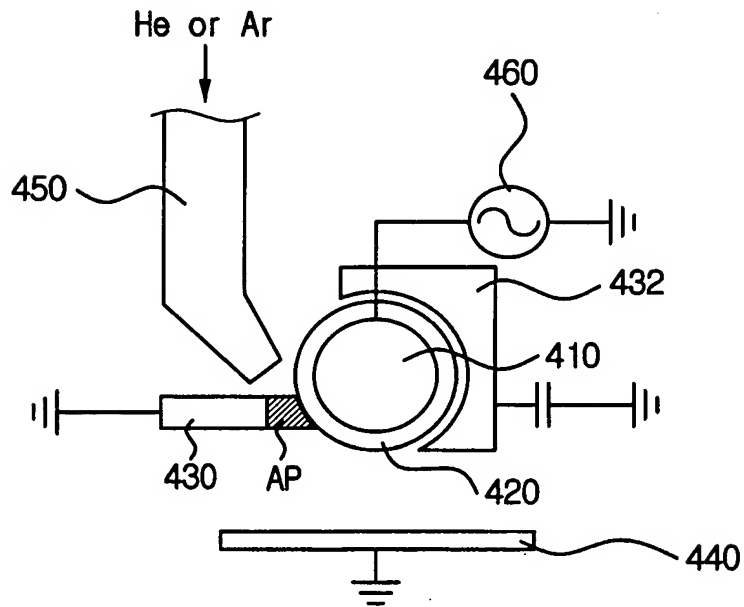
FIG. 15



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**FIG. 16**

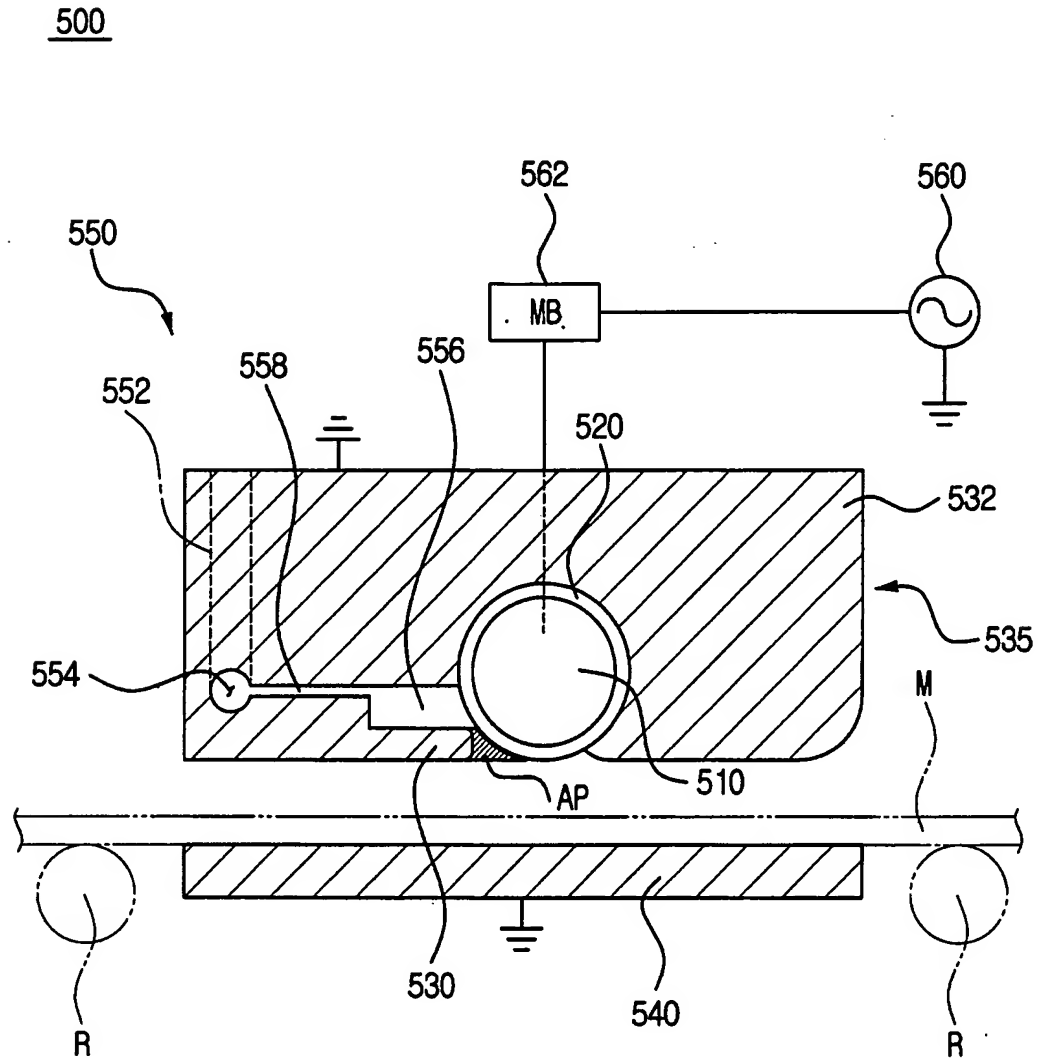
401





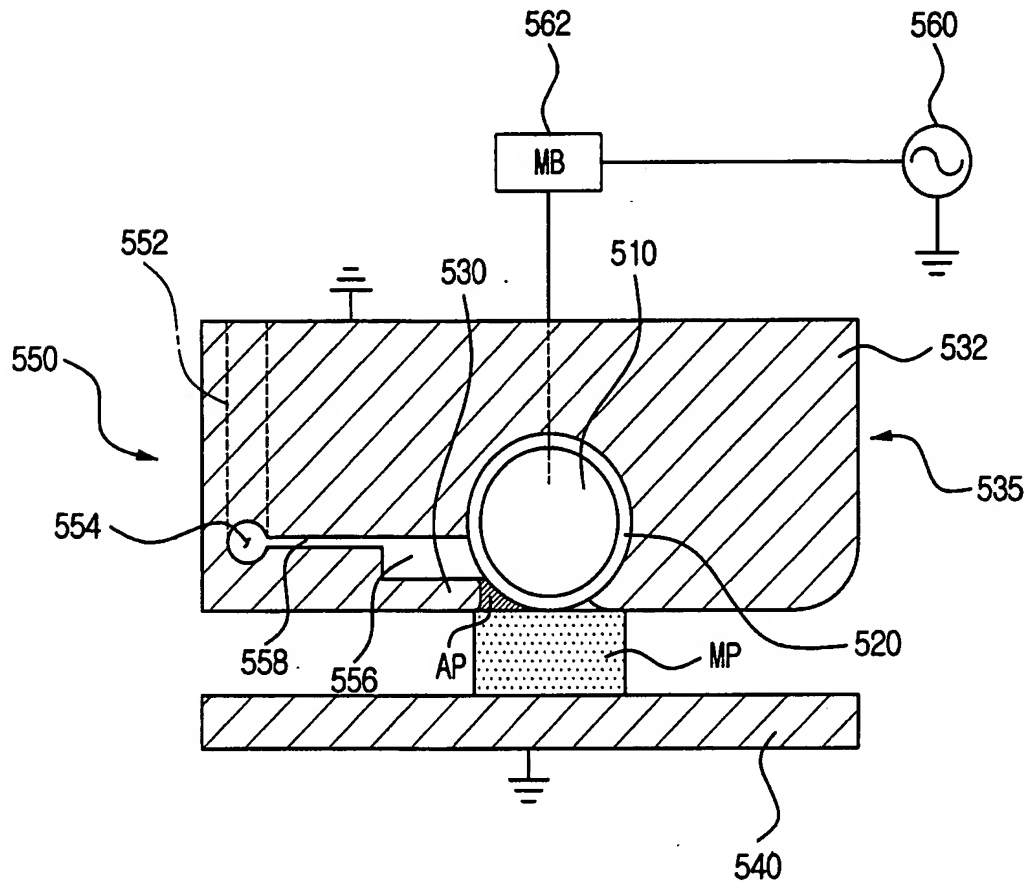
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FIG. 17



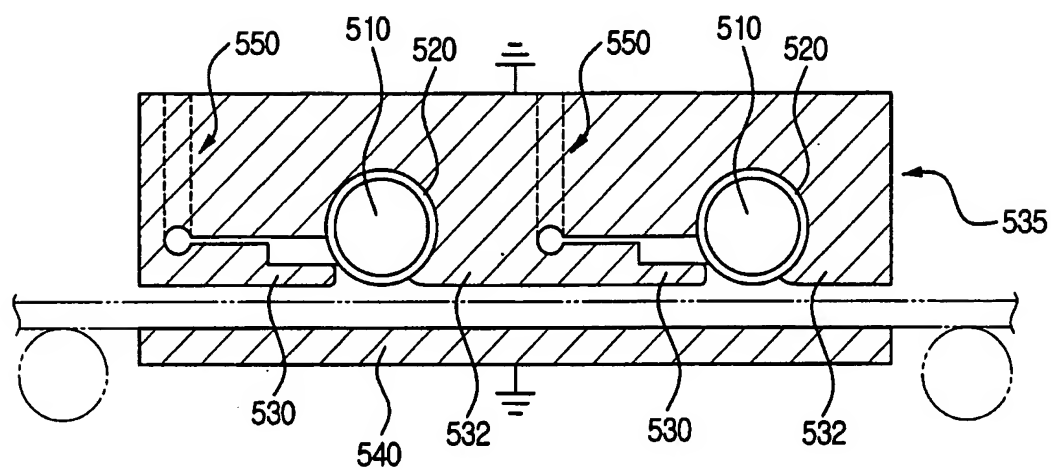
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FIG. 18



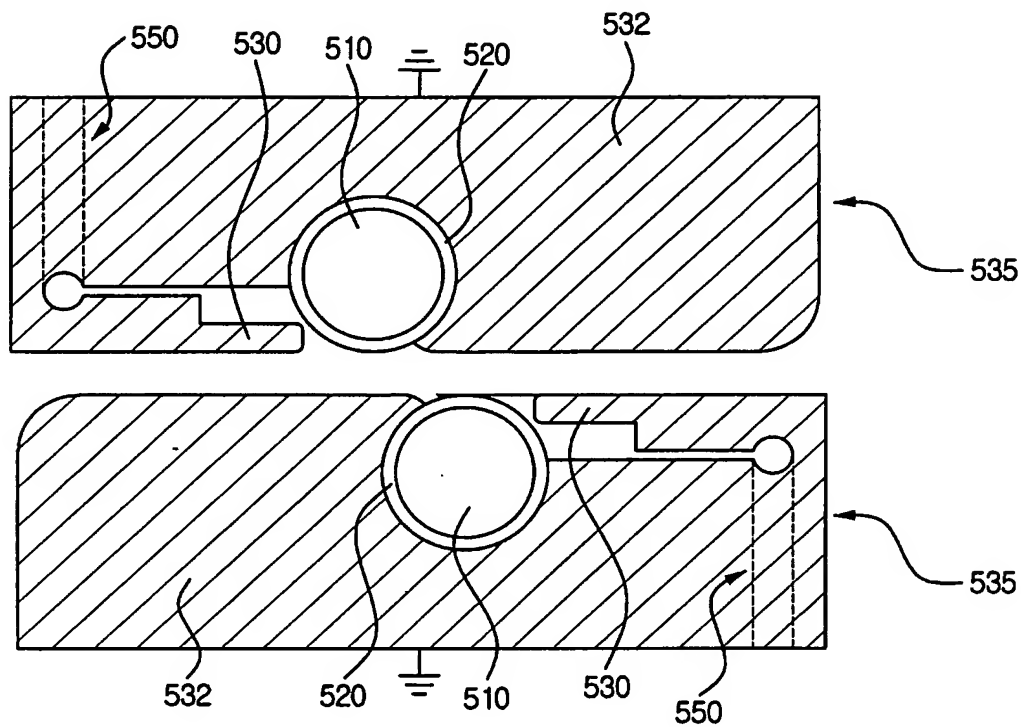
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**FIG. 19**



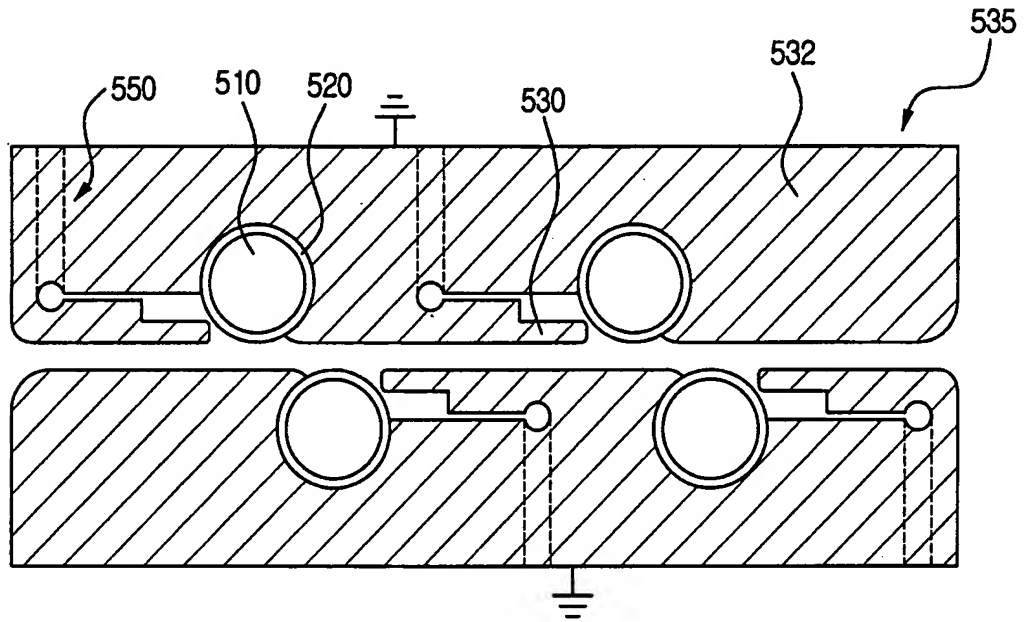
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**FIG. 20**



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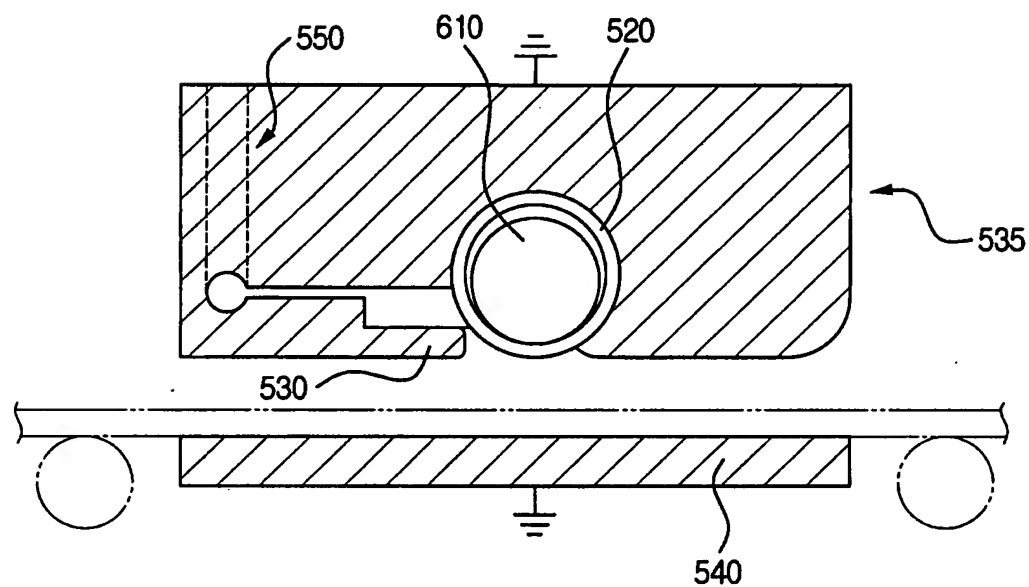
**FIG. 21**



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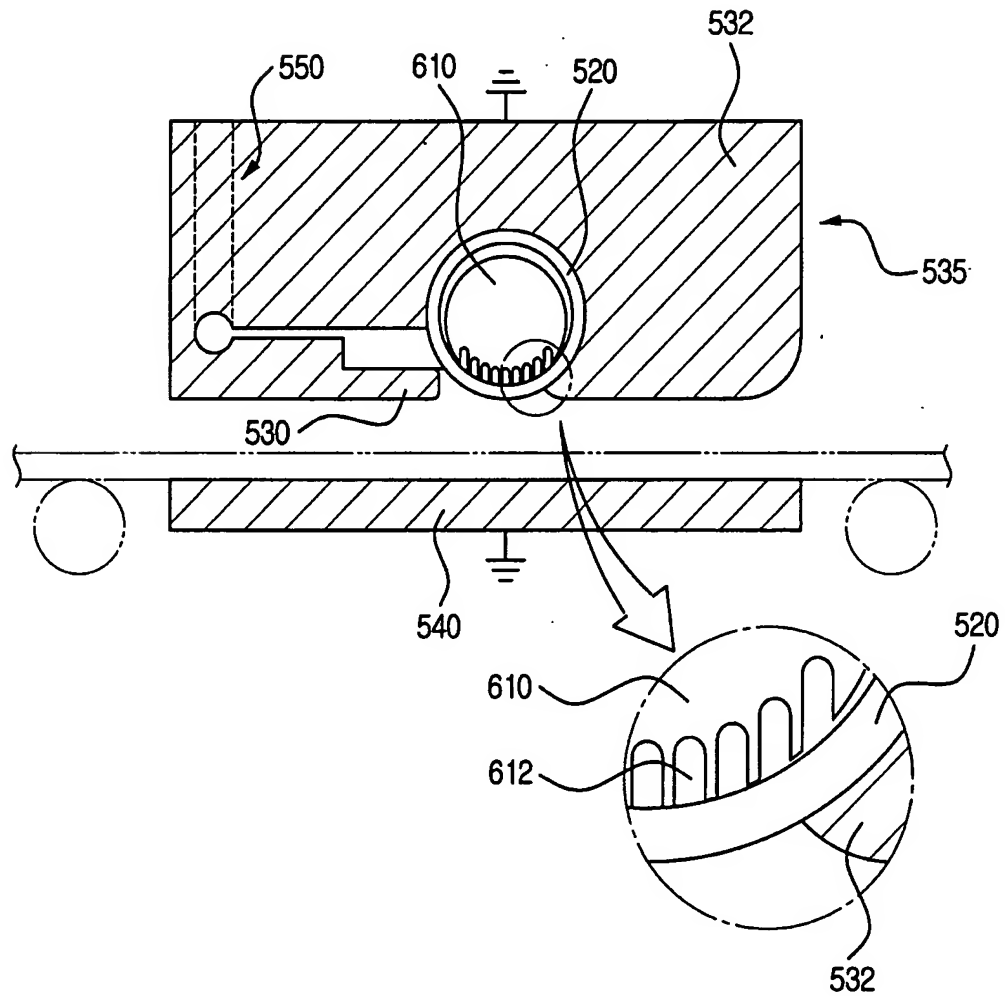
**FIG. 22**

600



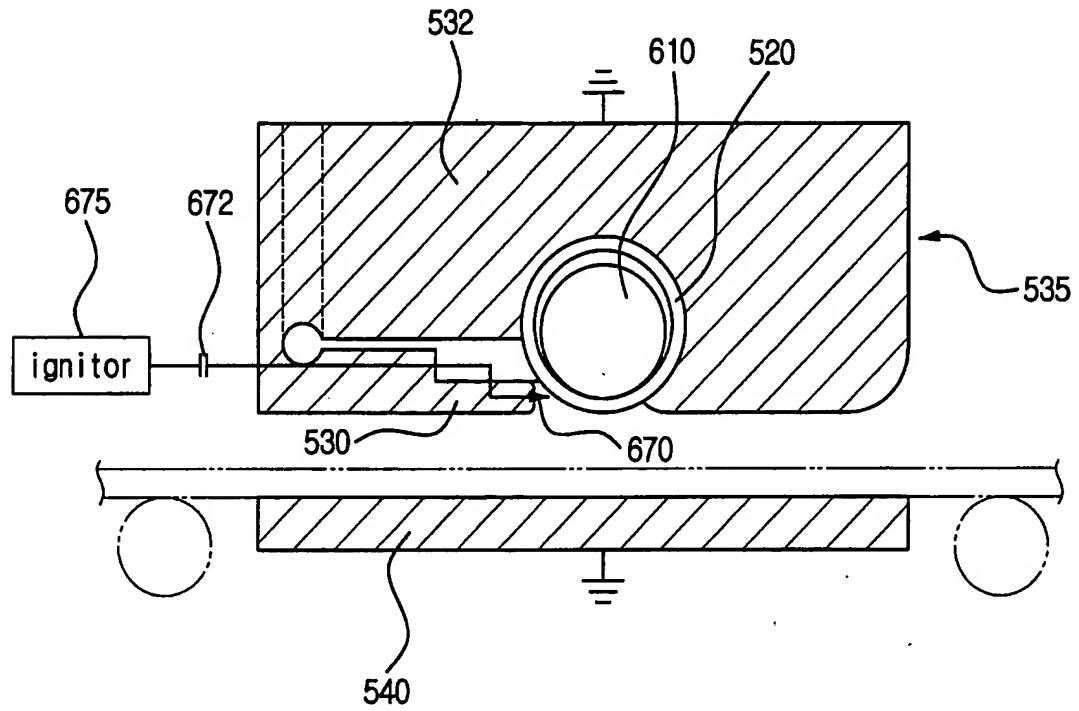
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**FIG. 23**



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**FIG. 24**





This diagram shows a cross-sectional view of a semiconductor device. A central circular region 520 is surrounded by a gate structure 510. The device is mounted on a substrate 530, which is supported by a base 540. A circuit is connected to the top surface, including a block MB, a voltage source 560, and a ground symbol. The device is also supported by rollers R.